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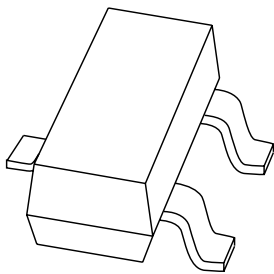
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Kind regards,

Team Nexperia

DATA SHEET



PMMT591A PNP BISS transistor

Product data sheet
Supersedes data of 2001 Jun 11

2004 Jan 13

PNP BISS transistor

PMMT591A

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

- Battery powered units where high current and low power consumption are important.

DESCRIPTION

PNP BISS (Breakthrough In Small Signal) transistor in a SOT23 plastic package. NPN complement: PMMT491A.

MARKING

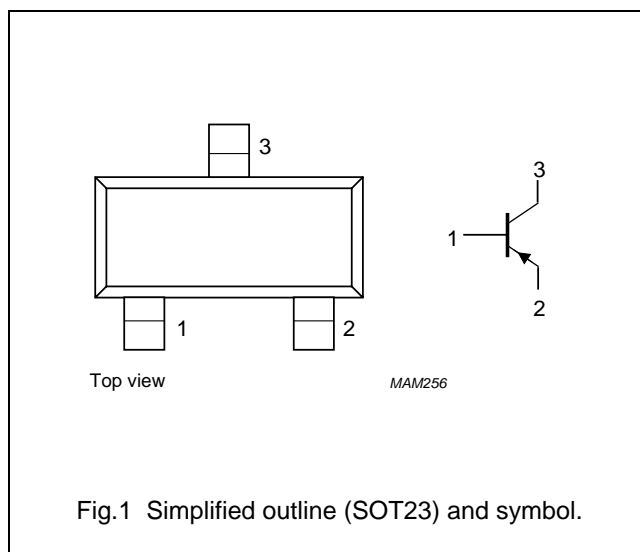
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMMT591A	9B*

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMMT591A	—	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	−40	V
V_{CEO}	collector-emitter voltage	open base	—	−40	V
V_{EBO}	emitter-base voltage	open collector	—	−5	V
I_C	collector current (DC)		—	−1	A
I_{CM}	peak collector current		—	−2	A
I_{BM}	peak base current		—	−1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP BISS transistor

PMMT591A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

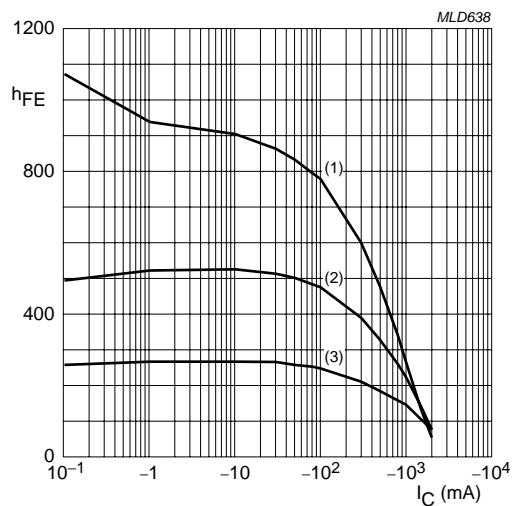
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -30\text{ V}$	–	–100	nA
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = -30\text{ V}$	–	–100	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -5\text{ V}$	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}$; note 1 $I_C = -1\text{ mA}$ $I_C = -100\text{ mA}$ $I_C = -500\text{ mA}$ $I_C = -1\text{ A}$	300 300 250 160	– 800 – –	
V_{CEsat}	collector-emitter saturation voltage	note 1 $I_C = -100\text{ mA}$; $I_B = -1\text{ mA}$ $I_C = -500\text{ mA}$; $I_B = -20\text{ mA}$ $I_C = -1\text{ A}$; $I_B = -100\text{ mA}$	– – –	–200 –350 –500	mV mV mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}$; $I_B = -50\text{ mA}$; note 1	–	–1.1	V
V_{BE}	base-emitter voltage	$V_{CE} = -5\text{ V}$; $I_C = -1\text{ A}$; note 1	–	–1	V
C_c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = -10\text{ V}$; $f = 1\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = -50\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 100\text{ MHz}$	150	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP BISS transistor

PMMT591A



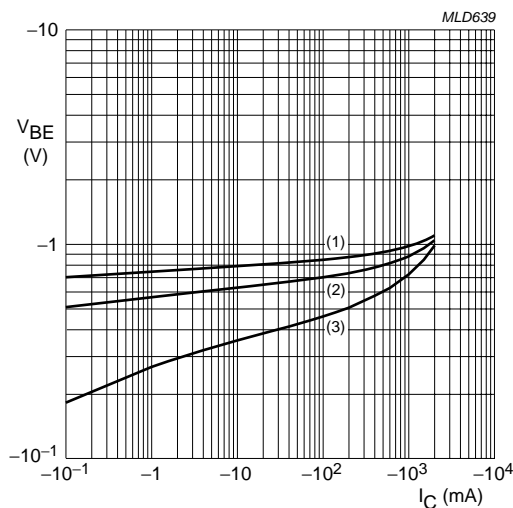
$V_{CE} = -5 \text{ V}$.

(1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.

Fig.2 DC current gain as a function of collector current; typical values.



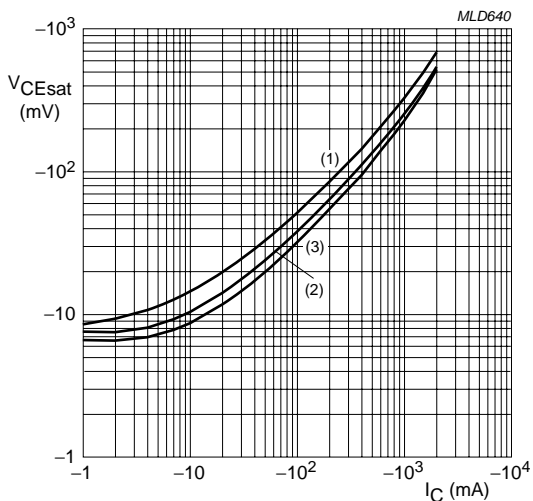
$V_{CE} = -5 \text{ V}$.

(1) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



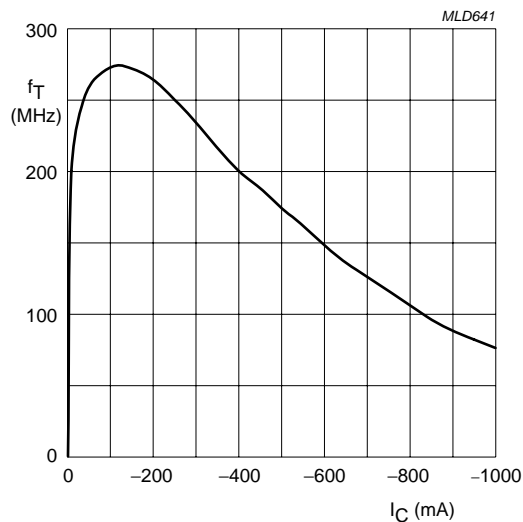
$I_C/I_B = 10$.

(1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

(3) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



$V_{CE} = -10 \text{ V}$.

Fig.5 Transition frequency as a function of collector current; typical values.

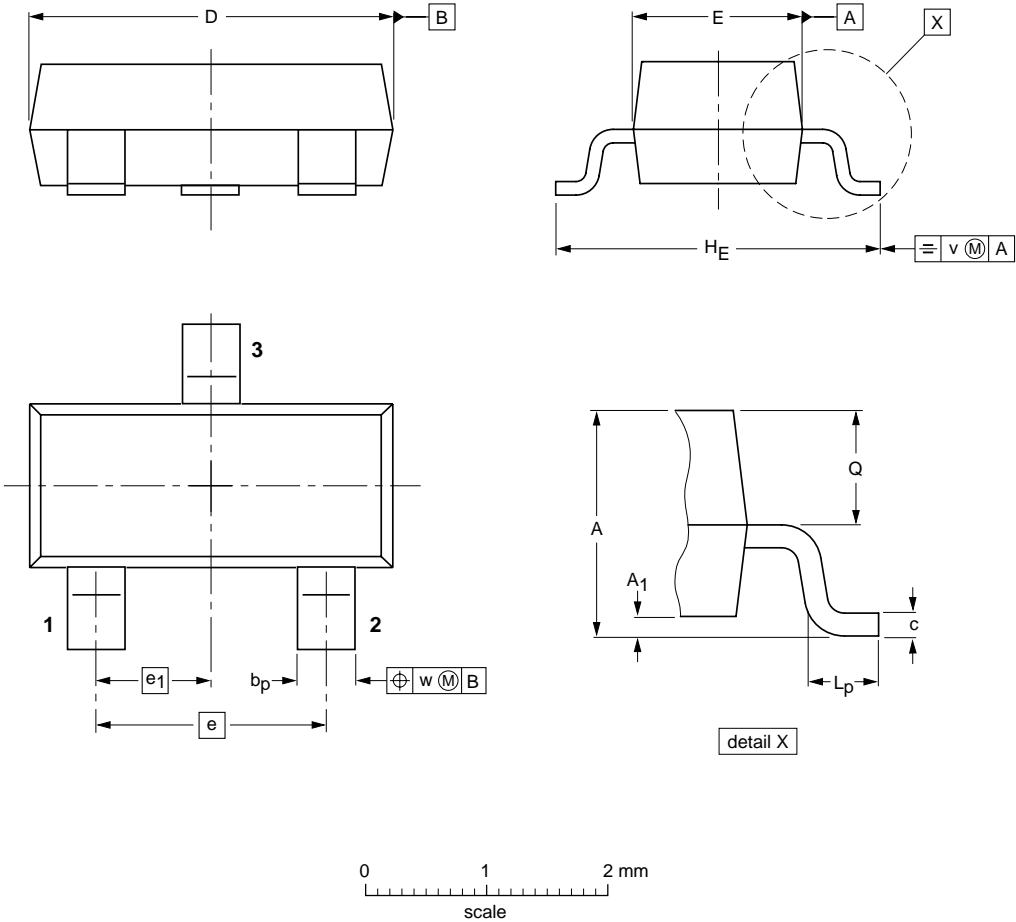
PNP BISS transistor

PMMT591A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

PNP BISS transistor

PMMT591A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: **<http://www.nxp.com>**

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.